



安徽富信半导体科技有限公司

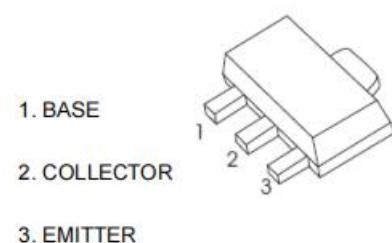
ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

2SA1661

SOT-89 Bipolar Transistor 双极型三极管

■ Features 特点

PNP High Voltage 高压



■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rating 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V _{CBO}	-120	V
Collector-Emitter Voltage 集电极发射极电压	V _{CEO}	-120	V
Emitter-Base Voltage 发射极基极电压	V _{EBO}	-5	V
Collector Current 集电极电流	I _C	-800	mA
Power dissipation 耗散功率	P _C (T _a =25°C)	500	mW
Thermal Resistance Junction-Ambient 热阻	R _{θJA}	250	°C/W
Junction and Storage Temperature 结温和储藏温度	T _J , T _{stg}	-55 to +150°C	

■ Device Marking 产品打标

H _{FE}	80-160(O)	120-240(Y)
Mark	DO.	DY.



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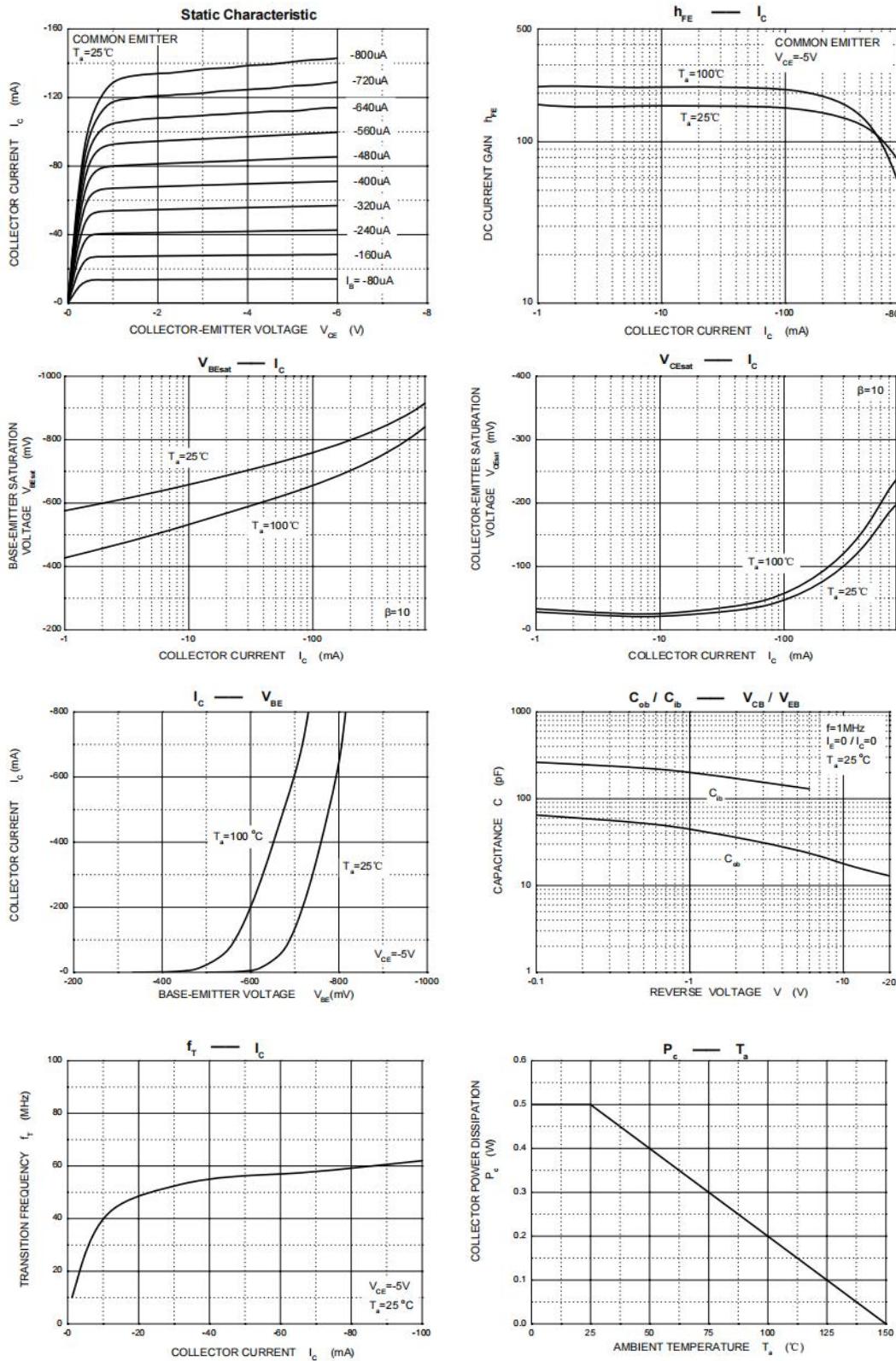
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■ Electrical Characteristics 电特性

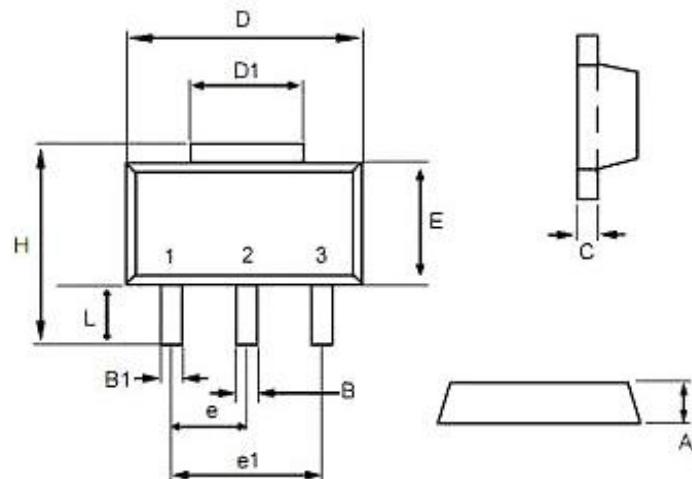
($T_A=25^\circ\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压($I_C = -1\text{mA}$, $I_E = 0$)	BV_{CBO}	-120	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压($I_C = -10\text{mA}$, $I_B = 0$)	BV_{CEO}	-120	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压($I_E = -1\text{mA}$, $I_C = 0$)	BV_{EBO}	-5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流($V_{\text{CB}} = -120\text{V}$, $I_E = 0$)	I_{CBO}	—	—	-100	nA
Emitter-Base Leakage Current 发射极基极漏电流($V_{\text{EB}} = -5\text{V}$, $I_C = 0$)	I_{EBO}	—	—	-100	nA
DC Current Gain 直流电流增益($V_{\text{CE}} = -5\text{V}$, $I_C = -100\text{mA}$)	H_{FE}	80	—	240	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降($I_C = -500\text{mA}$, $I_B = -50\text{mA}$)	$V_{\text{CE(sat)}}$	—	—	-1	V
Base-Emitter Saturation Voltage 基极发射极饱和压降($I_C = -500\text{mA}$, $I_B = -50\text{mA}$)	$V_{\text{BE(sat)}}$	—	—	-1	V
Base-Emitter On Voltage 基极发射极导通电压($V_{\text{CE}} = -5\text{V}$, $I_C = -500\text{mA}$)	$V_{\text{BE(on)}}$	—	—	-1	V
Transition Frequency 特征频率($V_{\text{CE}} = -5\text{V}$, $I_C = -100\text{mA}$)	f_T	—	120	—	MHz
Output Capacitance 输出电容($V_{\text{CB}} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$)	C_{ob}	—	30	—	pF

■ Typical Characteristic Curve 典型特性曲线



■ Dimension 外形封装尺寸



Dim	min	max
A	1.40	1.60
B	0.40	0.56
B1	0.35	0.48
C	0.35	0.44
D	4.40	4.60
D1	1.35	1.83
e	1.50 BSC	
e1	3.00 BSC	
E	2.29	2.60
H	3.75	4.25
L	0.80	1.20